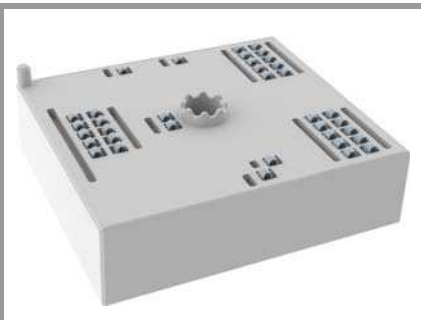


SKiiP 26GB07E3V1



MiniSKiiP® 2 Dual

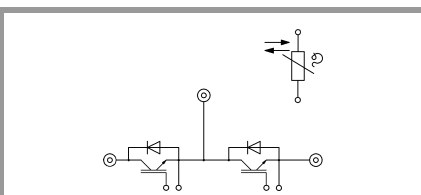
SKiiP 26GB07E3V1

Features

- 650V Trench IGBTs
- Robust and soft diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532
- NTC T-Sensor

Remarks

- Max. case temperature limited to $T_C=125^\circ\text{C}$
- Product reliability results valid for $T_j \leq 150^\circ\text{C}$ (recommended $T_{j,op} = -40 \dots +150^\circ\text{C}$)

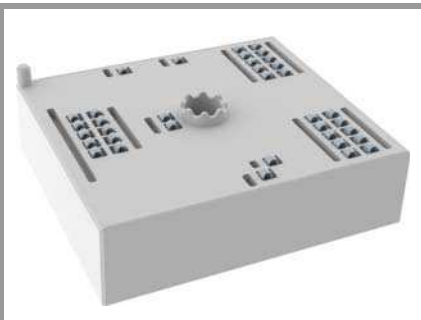


GB

Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
Inverter - IGBT			
V_{CES}	$T_j = 25^\circ\text{C}$	650	V
I_C	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	229
		$T_s = 70^\circ\text{C}$	183
I_{Cnom}		200	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$	600	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 360\text{ V}$	$T_j = 150^\circ\text{C}$	6
	$V_{GE} \leq 15\text{ V}$		
	$V_{CES} \leq 650\text{ V}$		
T_j		-40 ... 175	$^\circ\text{C}$
Inverse - Diode			
I_F	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	235
		$T_s = 70^\circ\text{C}$	184
I_{Fnom}		200	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	400	A
I_{FSM}	10 ms, sin 180°, $T_j = 150^\circ\text{C}$	1224	A
T_j		-40 ... 175	$^\circ\text{C}$
Module			
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$, 20 A per spring	200	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50 Hz, t = 1 min	2500	V

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
Inverter - IGBT					
$V_{CE(sat)}$	$I_C = 200\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.45	1.85	V
		$T_j = 150^\circ\text{C}$	1.70	2.10	V
V_{CE0}	chipelevel	$T_j = 25^\circ\text{C}$	0.9	1	V
		$T_j = 150^\circ\text{C}$	0.82	0.9	V
r_{CE}	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	2.8	4.3	m Ω
		$T_j = 150^\circ\text{C}$	4.4	6	m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 3.2\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 650\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
					mA
C_{ies}	$V_{CE} = 25\text{ V}$	f = 1 MHz	12.32		nF
C_{oes}	$V_{GE} = 0\text{ V}$	f = 1 MHz	0.77		nF
C_{res}		f = 1 MHz	0.37		nF
Q_G	- 8 V...+ 15 V		1600		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		1		Ω
$t_{d(on)}$	$V_{CC} = 300\text{ V}$ $I_C = 200\text{ A}$	$T_j = 150^\circ\text{C}$	64		ns
t_r	$R_{Gon} = 4\ \Omega$	$T_j = 150^\circ\text{C}$	62		ns
E_{on}	$R_{Goff} = 4\ \Omega$	$T_j = 150^\circ\text{C}$	4.4		mJ
$t_{d(off)}$	$di/dt_{on} = 4095\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	486		ns
t_f	$di/dt_{off} = 3935\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	60		ns
E_{off}	$V_{GE} = +15/-8\text{ V}$ $L_s = 25\text{ nH}$	$T_j = 150^\circ\text{C}$	7.4		mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste} = 0.8\text{ W/K}\cdot\text{m}$		0.28		K/W

SKiiP 26GB07E3V1



MiniSKiiP® 2 Dual

SKiiP 26GB07E3V1

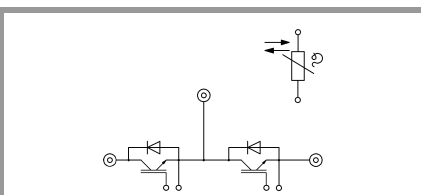
Features

- 650V Trench IGBTs
- Robust and soft diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532
- NTC T-Sensor

Remarks

- Max. case temperature limited to $T_C = 125^\circ\text{C}$
- Product reliability results valid for $T_j \leq 150^\circ\text{C}$ (recommended)
 $T_{j,op} = -40 \dots +150^\circ\text{C}$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse - Diode						
$V_F = V_{EC}$	$I_F = 200 \text{ A}$ $V_{GE} = 0 \text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$		1.4	1.8	V
		$T_j = 150^\circ\text{C}$		1.4	1.8	V
V_{F0}	chipllevel	$T_j = 25^\circ\text{C}$		1	1.2	V
		$T_j = 150^\circ\text{C}$		0.9	1	V
r_F	chipllevel	$T_j = 25^\circ\text{C}$		1.8	2.6	m Ω
		$T_j = 150^\circ\text{C}$		2.7	3.9	m Ω
I_{RRM}	$I_F = 200 \text{ A}$	$T_j = 150^\circ\text{C}$		190		A
Q_{rr}	$di/dt_{off} = 3754 \text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		20.6		μC
E_{rr}	$V_{GE} = -8 \text{ V}$ $V_{CC} = 300 \text{ V}$	$T_j = 150^\circ\text{C}$		4.5		mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste} = 0.8 \text{ W/K}\cdot\text{m}$			0.35		K/W
Module						
L_{CE}				20		nH
M_s	to heat sink		2		2.5	Nm
w				50		g
Temperature Sensor						
R_{100}	$T_c = 100^\circ\text{C}$ ($R_{25} = 5 \text{ k}\Omega$)			$493 \pm 5\%$		Ω
$B_{25/85}$	$R(T) = R_{25} \cdot \exp[B_{25/85} \cdot (1/T - 1/298)]$, [T]=K			3420		K



GB

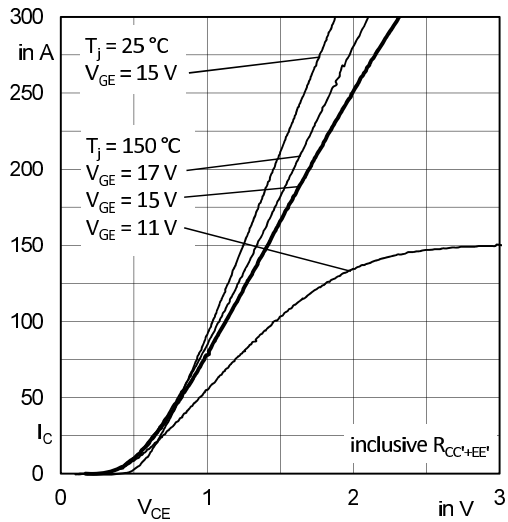


Fig. 1: Typ. output characteristic, inclusive R_{CC'+EE'}

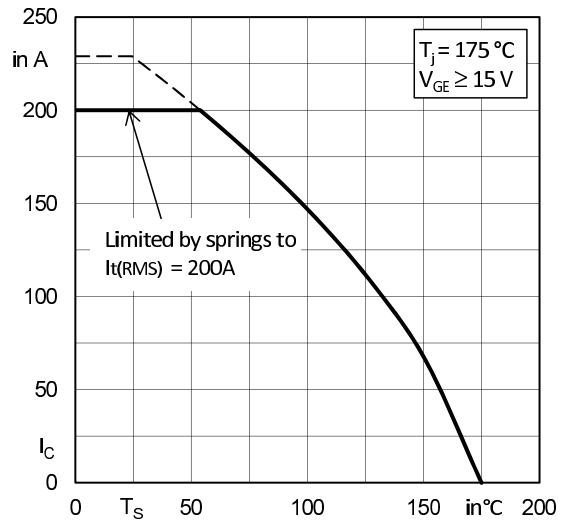


Fig. 2: Rated current vs. temperature I_C = f(T_S)

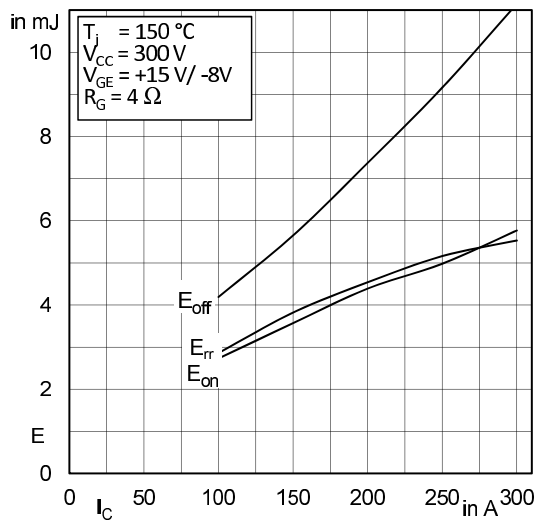


Fig. 3: Typ. turn-on /-off energy = f(I_C)

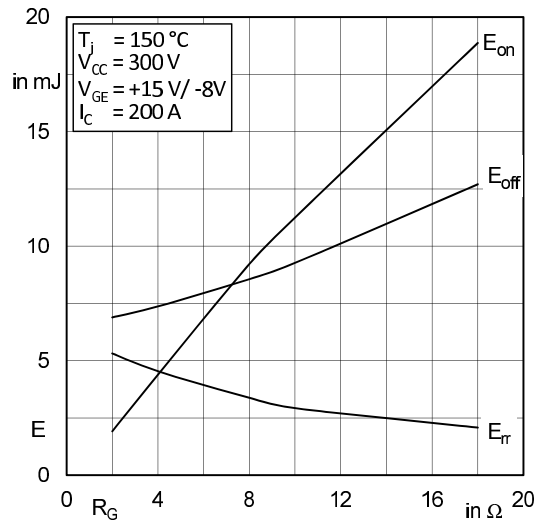


Fig. 4: Typ. turn-on /-off energy = f(R_G)

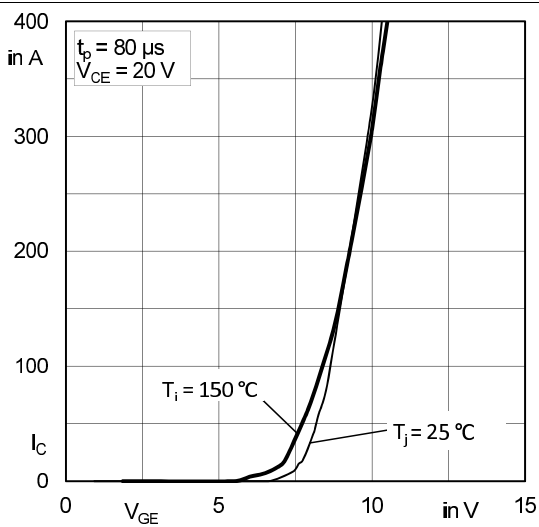


Fig. 5: Typ. transfer characteristic

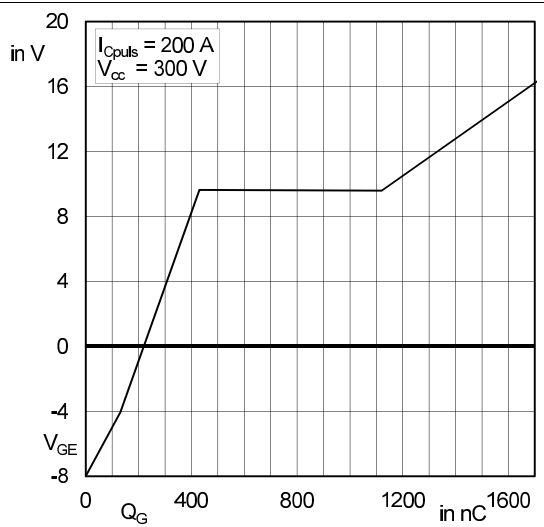


Fig. 6: Typ. gate charge characteristic

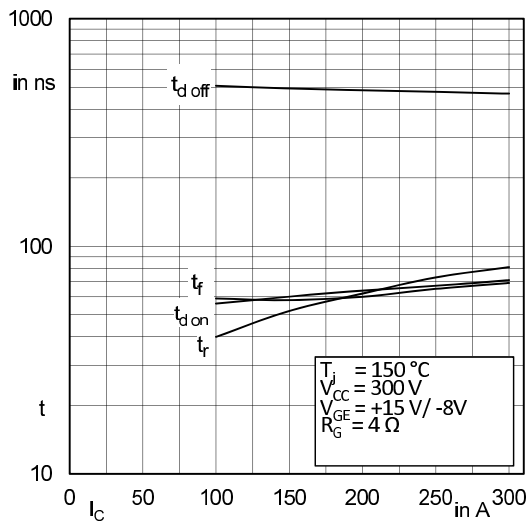


Fig. 7: Typ. switching times vs. I_C

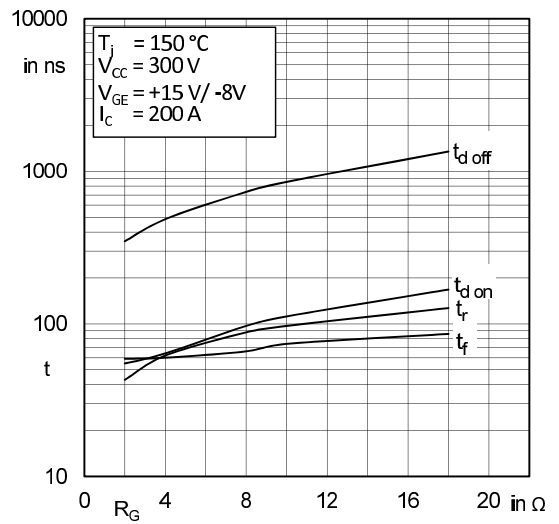


Fig. 8: Typ. switching times vs. gate resistor R_G

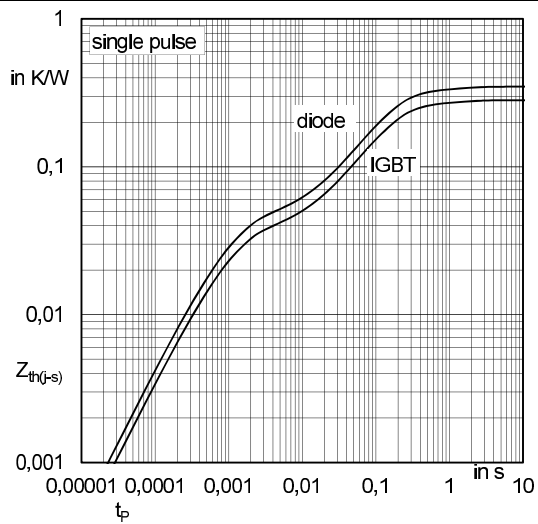


Fig. 9: Transient thermal impedance of IGBT and Diode

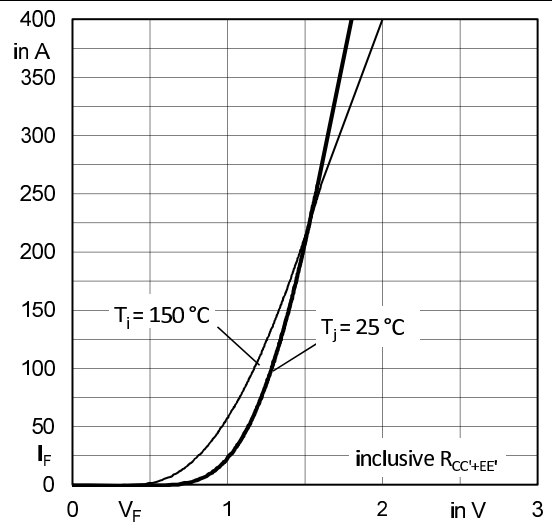


Fig. 10: CAL diode forward characteristic

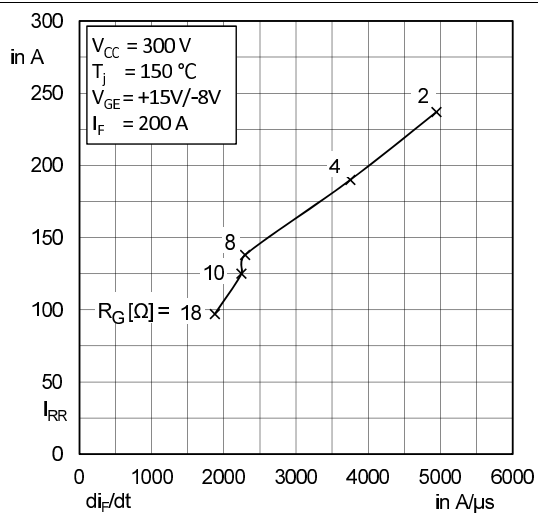


Fig. 11: Typ. CAL diode peak reverse recovery current

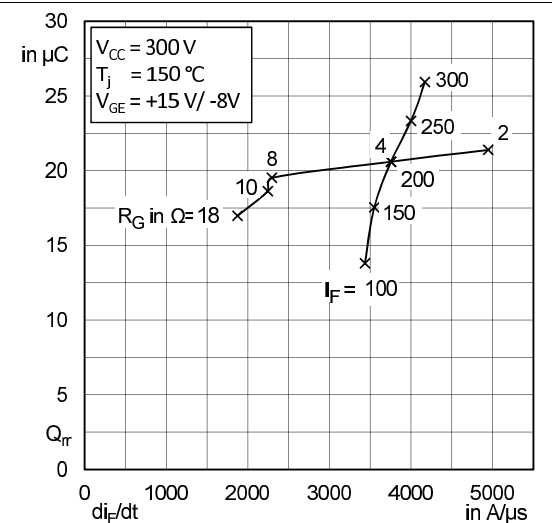
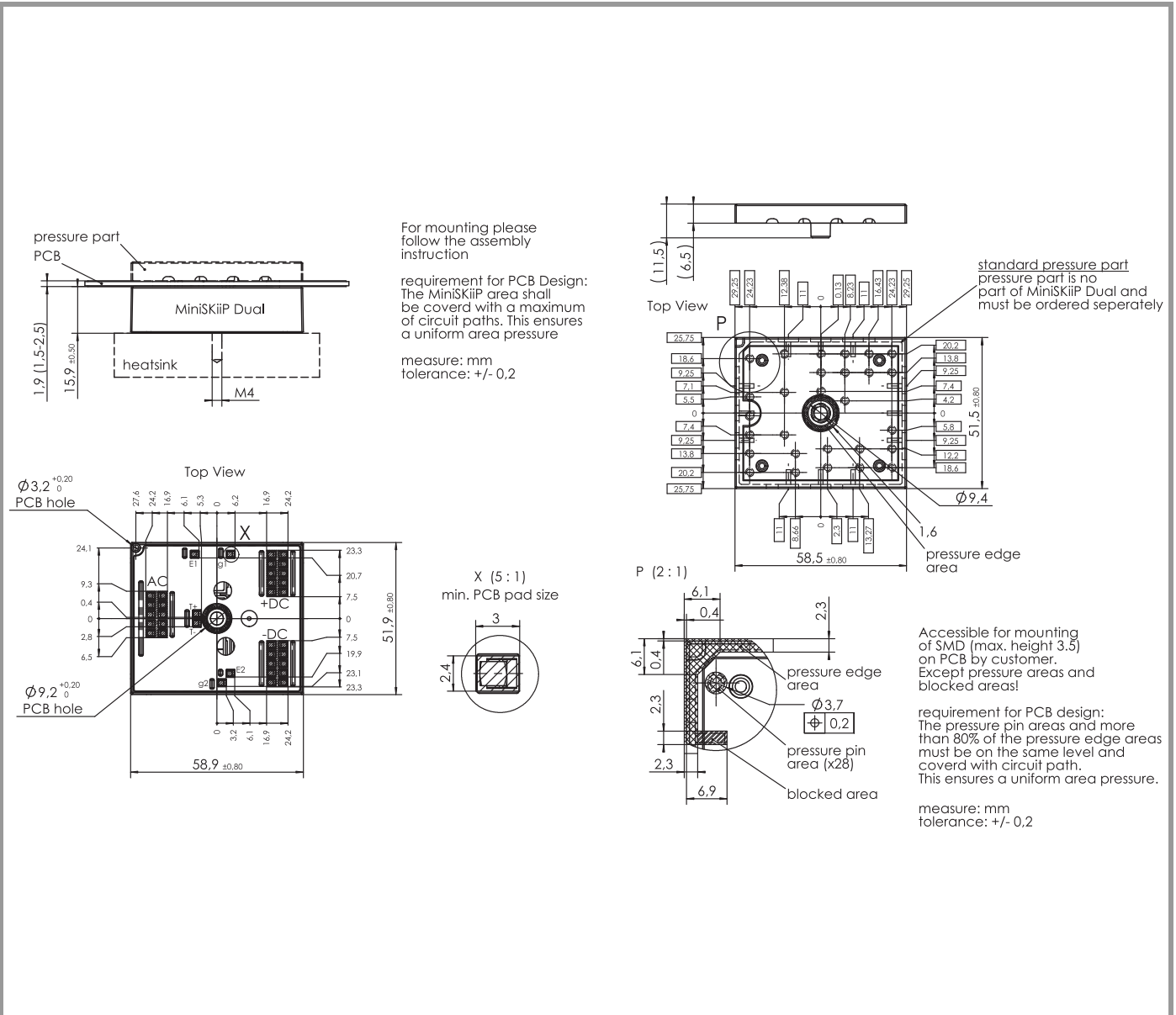
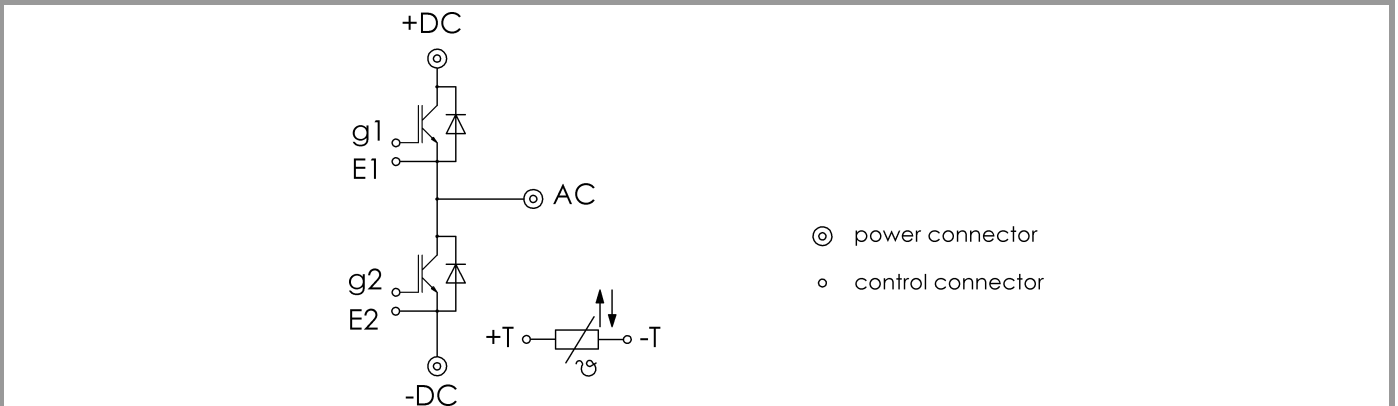


Fig. 12: Typ. CAL diode recovery charge

SKiiP 26GB07E3V1



pinout, dimensions



pinout

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.